/ Descriptions

TO-252 SiC

SiC Schottky Barrier Diode in a TO-252 Plastic Package.

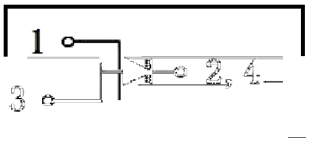
/ Features

Low power loss, high efficiency, HF Product.

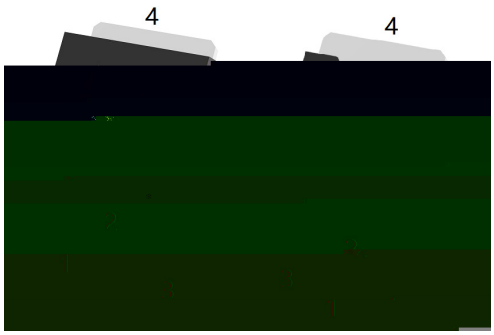
/ Applications

For high frequency, high voltage, high current rectifier diode, freewheeling diode

/ Equivalent Circuit



/ Pinning



PIN1 3 Anode PIN 2 4 Cathode

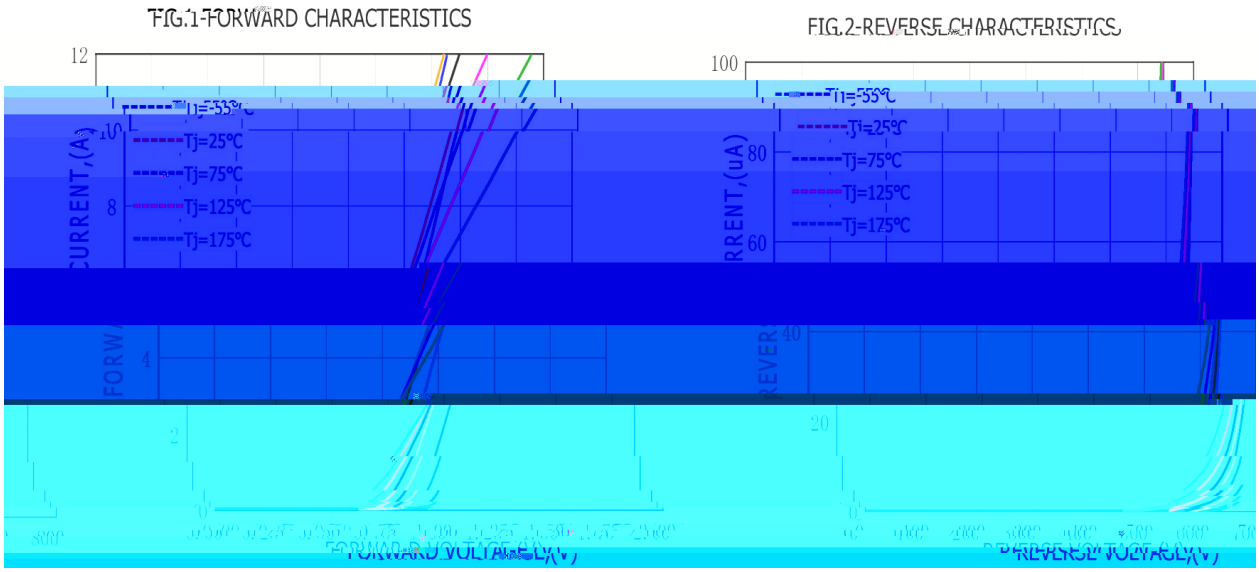
/ Marking

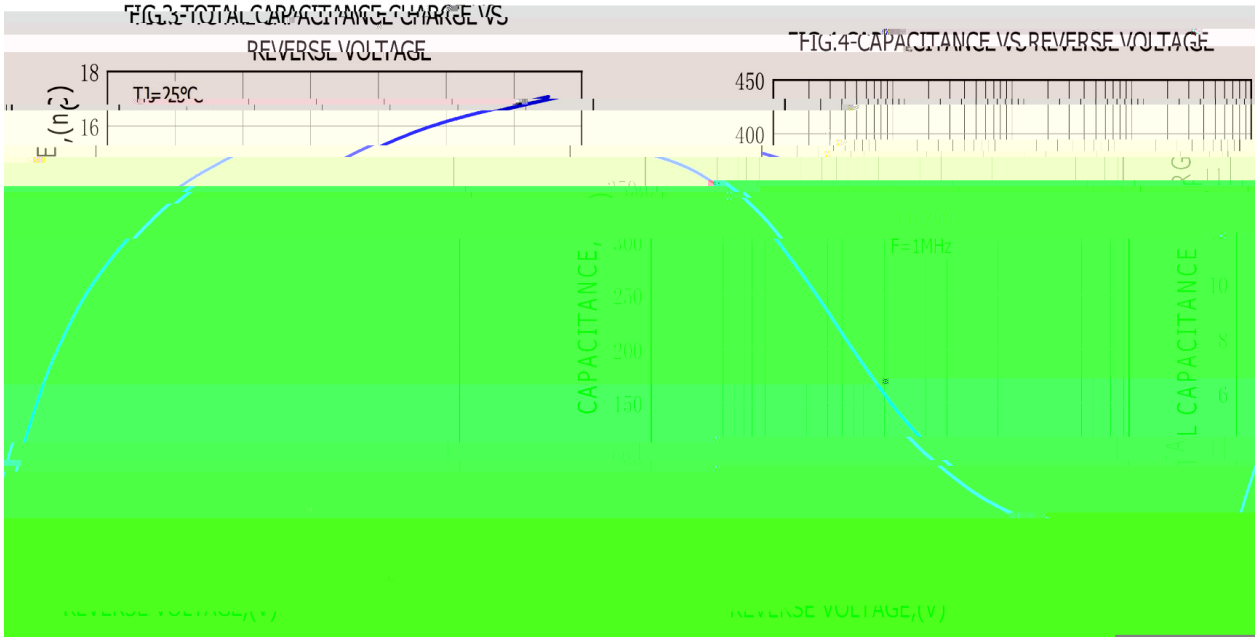
See Marking Instructions.

Parameter	Symbol	Rating	Unit
Peak Repetitive Reverse Voltage	V_{RRM}	650	V
Maximum RMS Voltage	V_{RMS}	455	V
Maximum DC blocking Voltage	V_{DC}	650	V
Continuous Forward Current,T_C=150	I_F	6	A
Peak forward surge current,tp=8.3ms	I_{FSM}	52	A
Total power disspation	P_D	53	W
Typical Thermal Resistance Junction to Case	R θ JC	2.8	/W
Operation Junction Temperature and Storage Temperature	T_J, T_{STG}	-55~+175	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit

/ Electrical Characteristic Curve





/ Package Dimensions

BRSC06650DP
Rev.A Aug.-2024